NLAS324

Dual SPST Analog Switch, Low Voltage, Single Supply

The NLAS324 is a dual SPST (Single Pole, Single Throw) switch, similar to 1/2 a standard 4066. The device permits the independent selection of 2 analog/digital signals. Available in the Ultra−Small 8 package.

The use of advanced 0.6 μ CMOS process, improves the R_{ON} resistance considerably compared to older higher voltage technologies.

Features

- On Resistance is 20 Ω Typical at 5.0 V
- Matching is < Ω Between Sections
- 2 − 6 V Operating Range
- Ultra Low < 5 pC Charge Injection
- Ultra Low Leakage < 1 nA at 5.0 V, 25°C
- Wide Bandwidth > 200 MHz, −3 dB
- 2000 V ESD (HBM)
- Ron Flatness ± 6 Ω at 5.0 V
- US8 Package
- Negative Enable
- Switches are Independent
- Pb−Free Package is Available

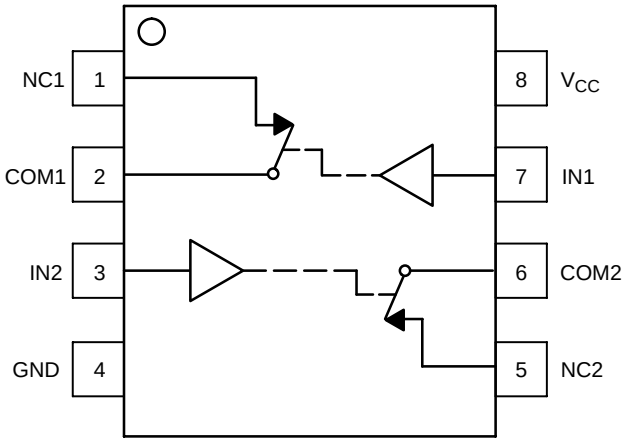

Figure 1. Pinout

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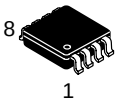
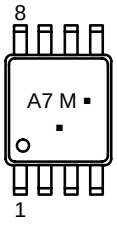
MARKING DIAGRAM



US8
US SUFFIX
CASE 493



A7 = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

PIN ASSIGNMENT

1	NC1
2	COM1
3	IN2
4	GND
5	NC2
6	COM2
7	IN1
8	V_{CC}

FUNCTION TABLE

On/Off Enable Input	State of Analog Switch
L	On
H	Off

ORDERING INFORMATION

Device	Package	Shipping†
NLAS324US	US8	3,000 / Tape & Reel
NLAS324USG	US8 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_I	DC Input Voltage		−0.5 to +7.0	V
V_O	DC Output Voltage		−0.5 to +7.0	V
I_{IK}	DC Input Diode Current	V_I < GND	−50	mA
I_{OK}	DC Output Diode Current	V_O < GND	−50	mA
I_O	DC Output Sink Current		±50	mA
I_{CC}	DC Supply Current per Supply Pin		±100	mA
I_{GND}	DC Ground Current per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 1)		250	°C/W
P_D	Power Dissipation in Still Air at 85°C		250	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating Oxygen Index: 28 to 34		UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 150 N/A	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2−ounce copper trace with no air flow.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to JESD22−C101−A.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		2.0	5.5	V
V_{IN}	Digital Input Voltage (Enable)		GND	5.5	V
V_{IO}	Static or Dynamic Voltage Across an Off Switch		GND	V_{CC}	V
V_{IS}	Analog Input Voltage (NO, COM)		GND	V_{CC}	V
T_A	Operating Temperature Range, All Package Types		−55	+125	°C
t_r, t_f	Input Rise or Fall Time, (Enable Input)	V_{cc} = 3.3 V ± 0.3 V V_{cc} = 5.0 V ± 0.5 V	0 0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

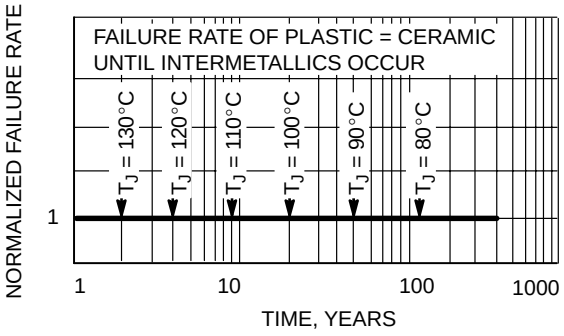


Figure 2. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS − Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V_{CC}	Guaranteed Max Limit			Unit
				−55 to 25°C	<85°C	<125°C	
V_{IH}	Minimum High−Level Input Voltage, Enable Inputs		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85	1.5 2.1 3.15 3.85	1.5 2.1 3.15 3.85	V
V_{IL}	Maximum Low−Level Input Voltage, Enable Inputs		2.0 3.0 4.5 5.5	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	V
I_{IN}	Maximum Input Leakage Current, Enable Inputs	V_{IN} = 5.5 V or GND	0 V to 5.5 V	±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per package)	Enable and V_{IS} = V_{CC} or GND	5.5	1.0	1.0	2.0	μA

DC ELECTRICAL CHARACTERISTICS − Analog Section

Symbol	Parameter	Condition	V_{CC}	Guaranteed Max Limit			Unit
				−55 to 25°C	<85°C	<125°C	
R_{ON}	Maximum ON Resistance (Figures 8 − 12)	V_{IN} = V_{IH} V_{IS} = V_{CC} to GND I_{Is}I = ≤10.0mA	3.0 4.5 5.5	45 30 25	50 35 30	55 40 35	Ω
$R_{FLAT(ON)}$	ON Resistance Flatness	V_{IN} = V_{IH} I_{Is}I = ≤10.0mA V_{IS} = 1V, 2V, 3.5V	4.5	4	4	5	Ω
$I_{NO(OFF)}$	Off Leakage Current, Pin 2 (Figure 3)	V_{IN} = V_{IL} V_{NO} = 1.0 V, V_{COM} = 4.5 V or V_{COM} = 1.0 V and V_{NO} 4.5 V	5.5	1	10	100	nA
$I_{COM(OFF)}$	Off Leakage Current, Pin 1 (Figure 3)	V_{IN} = V_{IL} V_{NO} = 4.5 V or 1.0 V V_{COM} = 1.0 V or 4.5 V	5.5	1	10	100	nA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	Test Conditions	V_{CC} (V)	Guaranteed Max Limit									Unit
				−55 to 25°C			<85°C			<125°C			
				Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_{ON}	Turn−On Time	R_L = 300 Ω, C_L = 35 pF (Figures 4, 5, and 13)	2.03.04.55.5		7.0 5.0 4.5 4.5	14 10 9 9			16 12 11 11			16 12 11 11	ns
t_{OFF}	Turn−Off Time	R_L = 300 Ω, C_L = 35 pF (Figures 4, 5, and 13)	2.03.04.5 5.5		11.0 7.0 5.0 5.0	22 14 10 10			24 16 12 12			24 16 12 12	ns

		Typical @ 25, V_{CC} = 5.0 V	
C_{IN}	Maximum Input Capacitance, Select Input	8	pF
$C_{NO\ or}$ C_{NC}	Analog I/O (switch off)	10	
$C_{COM(OFF)}$	Common I/O (switch off)	10	
$C_{COM(ON)}$	Feedthrough (switch on)	20	

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

Symbol	Parameter	Condition	V_{CC} V	Limit 25°C	Unit
BW	Maximum On−Channel −3dB Bandwidth or Minimum Frequency Response	V_{IS} = 0 dBm V_{IS} centered between V_{CC} and GND (Figures 6 and 14)	3.0 4.5 5.5	190 200 220	MHz
V_{ONL}	Maximum Feedthrough On Loss	V_{IS} = 0 dBm @ 10 kHz V_{IS} centered between V_{CC} and GND (Figure 6)	3.0 4.5 5.5	−2 −2 −2	dB
V_{ISO}	Off−Channel Isolation	f = 100 kHz; V_{IS} = 1 V RMS V_{IS} centered between V_{CC} and GND (Figures 6 and 15)	3.0 4.5 5.5	−93	dB
Q	Charge Injection Enable Input to Common I/O	V_{IS} = V_{CC} to GND, F_{IS} = 20 kHz $t_r = t_f$ = 3 ns R_{IS} = 0 Ω, C_L = 1000 pF Q = C_L * ΔV_{OUT} (Figures 7 and 16)	3.0 5.5	1.5 3.0	pC
THD	Total Harmonic Distortion THD + Noise	F_{IS} = 20 Hz to 1 MHz, R_L = Rgen = 600 Ω, C_L = 50 pF V_{IS} = 3.0 V_{PP} sine wave V_{IS} = 5.0 V_{PP} sine wave (Figure 17)	3.3 5.5	0.3 0.15	%

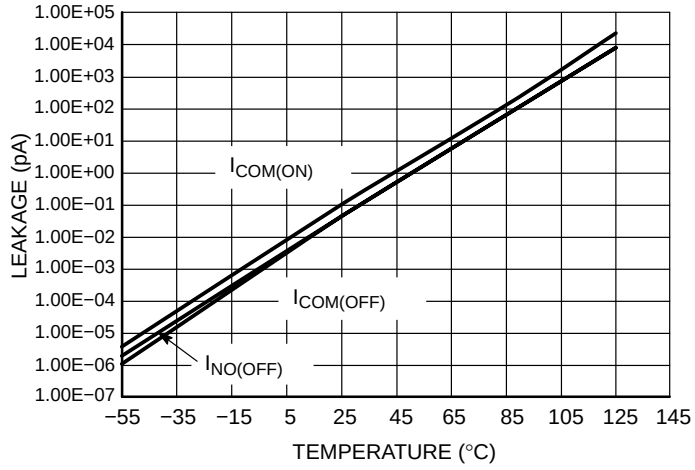


Figure 3. Switch Leakage vs. Temperature

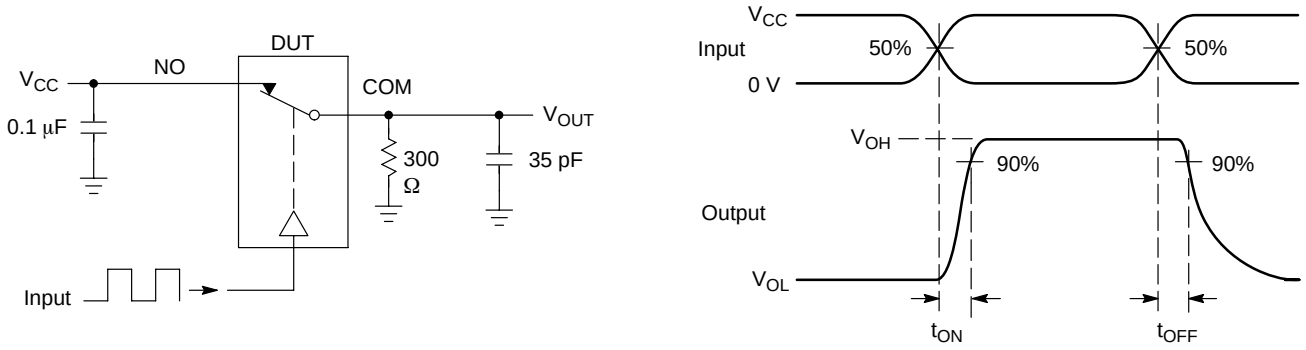


Figure 4. t_{ON}/t_{OFF}

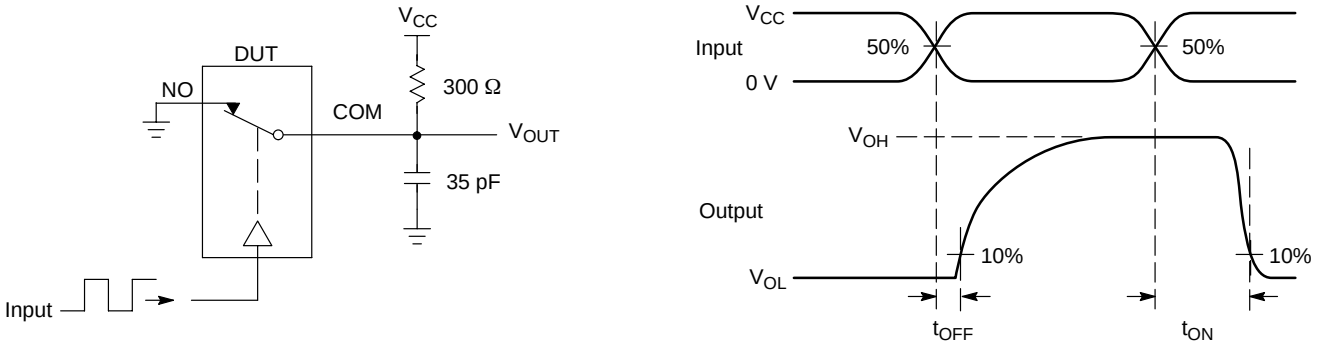
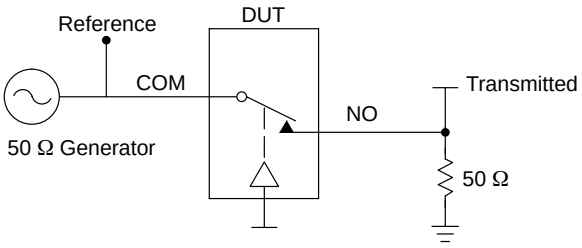


Figure 5. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO}, Bandwidth and V_{ONL} are independent of the input signal direction.

V_{ISO} = Off Channel Isolation = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz

V_{ONL} = On Channel Loss = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz to 50 MHz

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

Figure 6. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

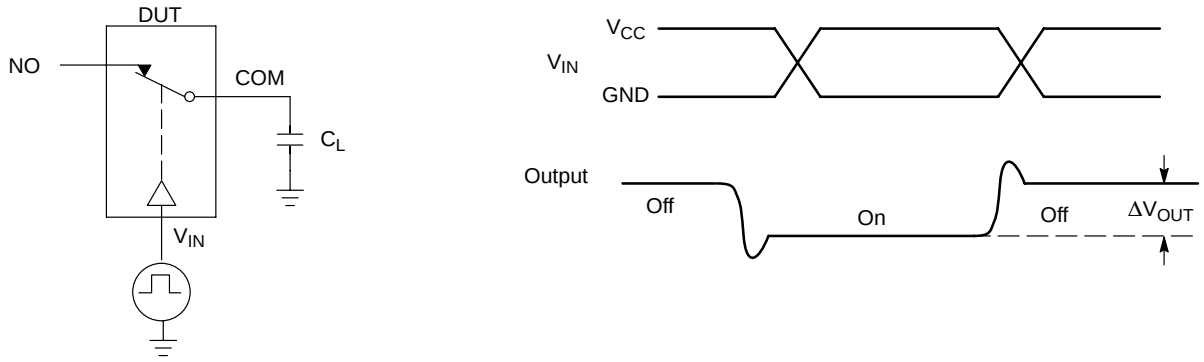


Figure 7. Charge Injection: (Q)

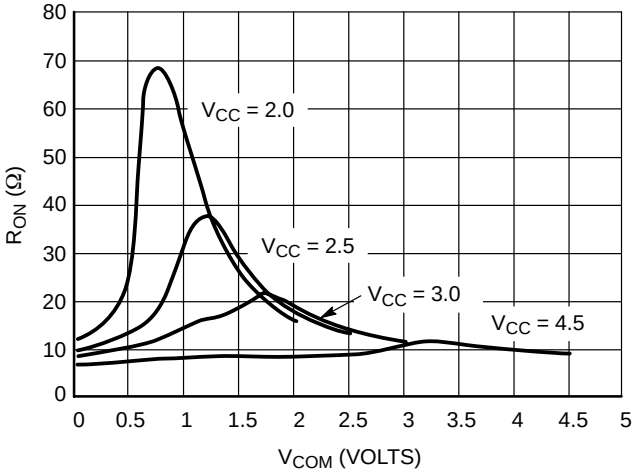


Figure 8. R_{ON} vs. V_{COM} and V_{CC} (@25°C)

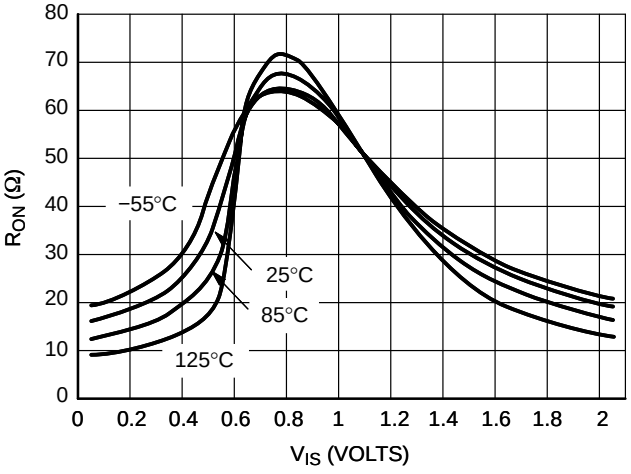


Figure 9. R_{ON} vs. V_{COM} and Temperature, V_{CC} = 2.0 V

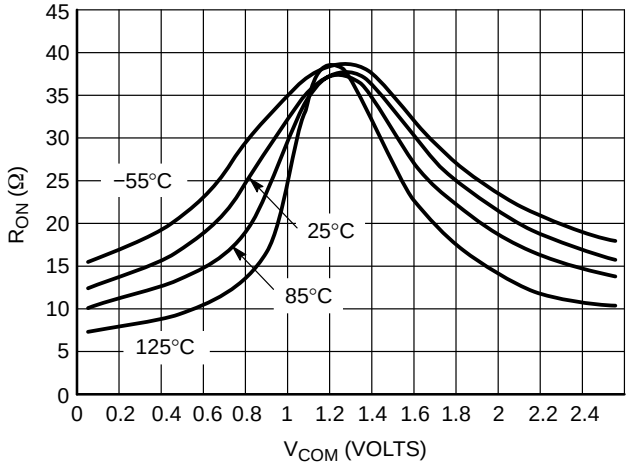


Figure 10. R_{ON} vs. V_{COM} and Temperature, V_{CC} = 2.5 V

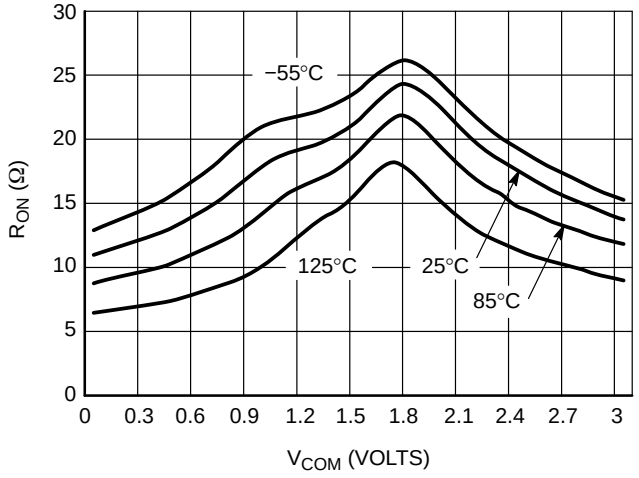


Figure 11. R_{ON} vs. V_{COM} and Temperature, V_{CC} = 3.0 V

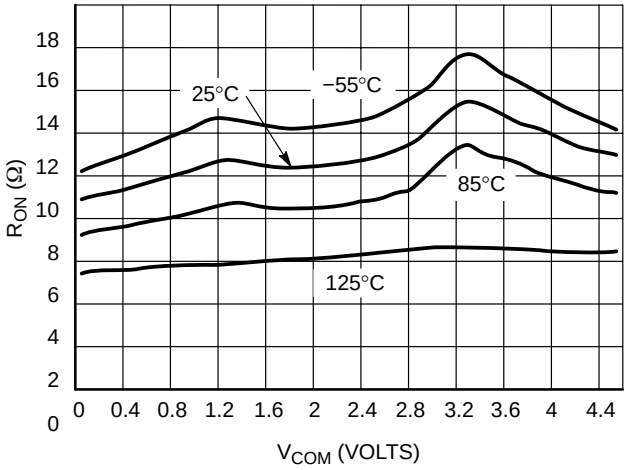


Figure 12. R_{ON} vs. V_{COM} and Temperature, V_{CC} = 4.5 V

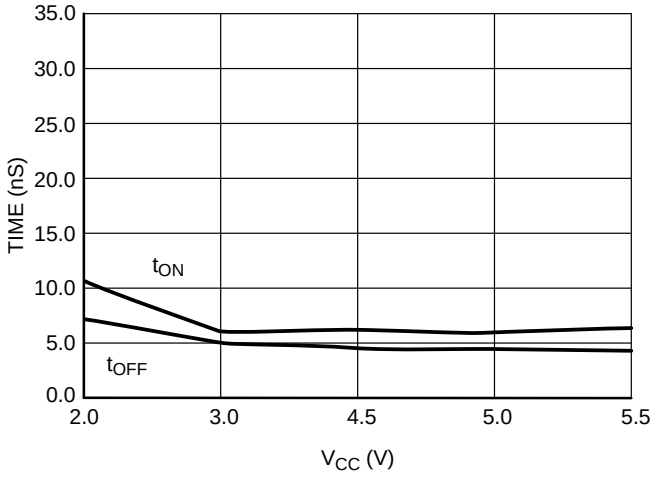


Figure 13. Switching Time vs. Supply Voltage, T = 25°C

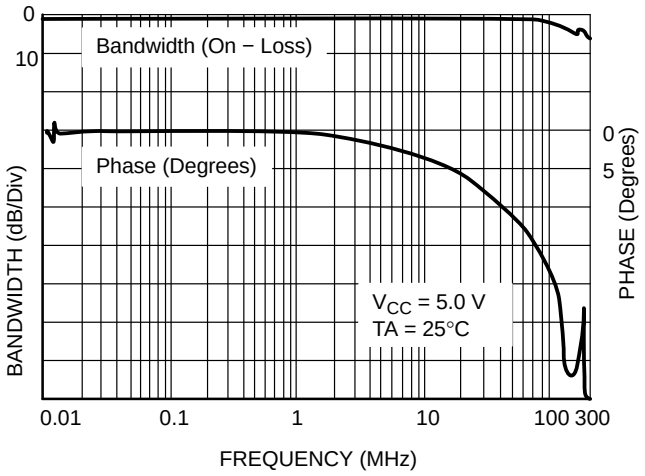


Figure 14. ON Channel Bandwidth and Phase Shift Over Frequency

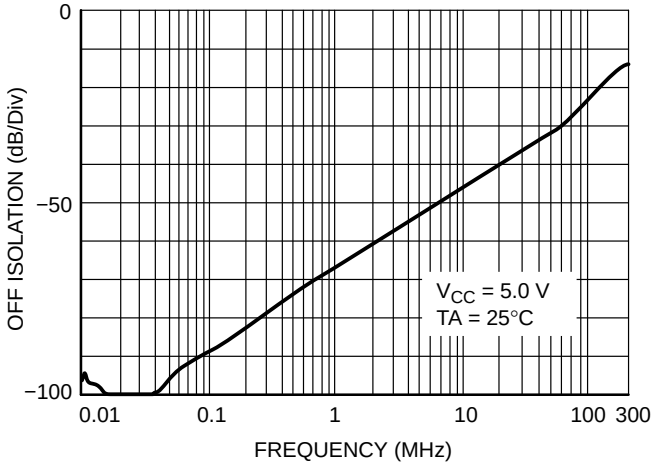


Figure 15. Off Channel Isolation

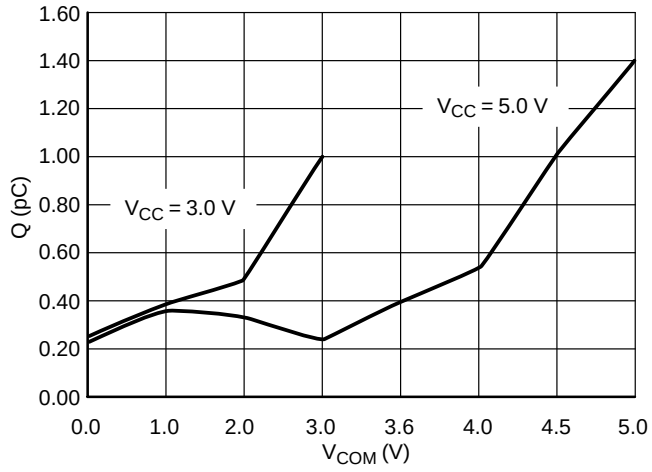


Figure 16. Charge Injection vs. V_{COM}

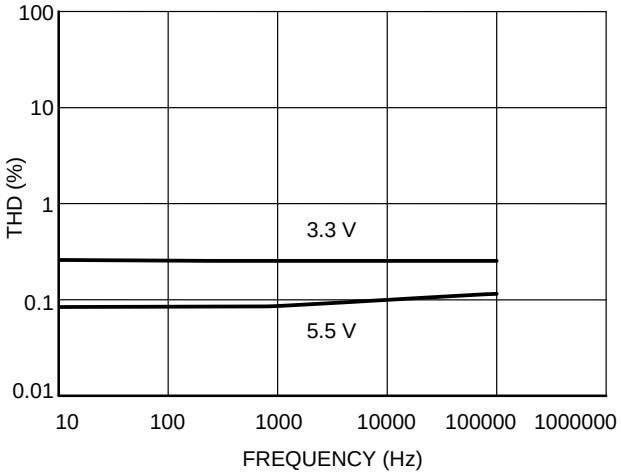


Figure 17. THD vs. Frequency

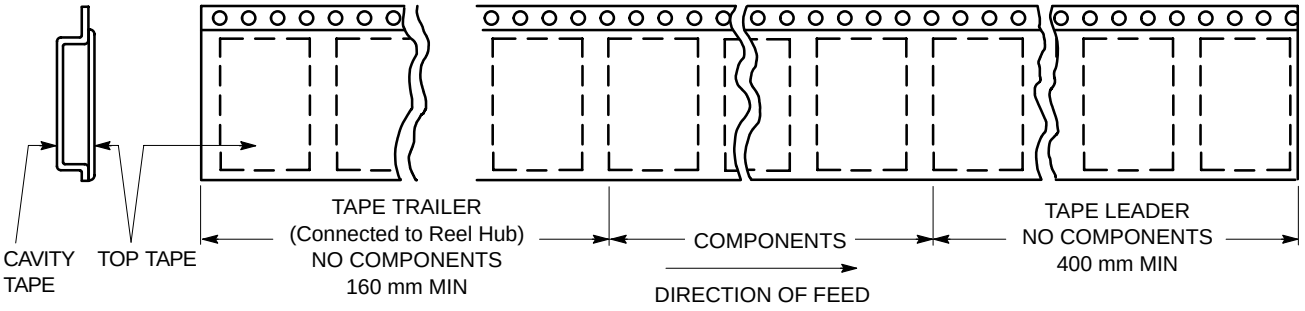


Figure 18. Tape Ends for Finished Goods

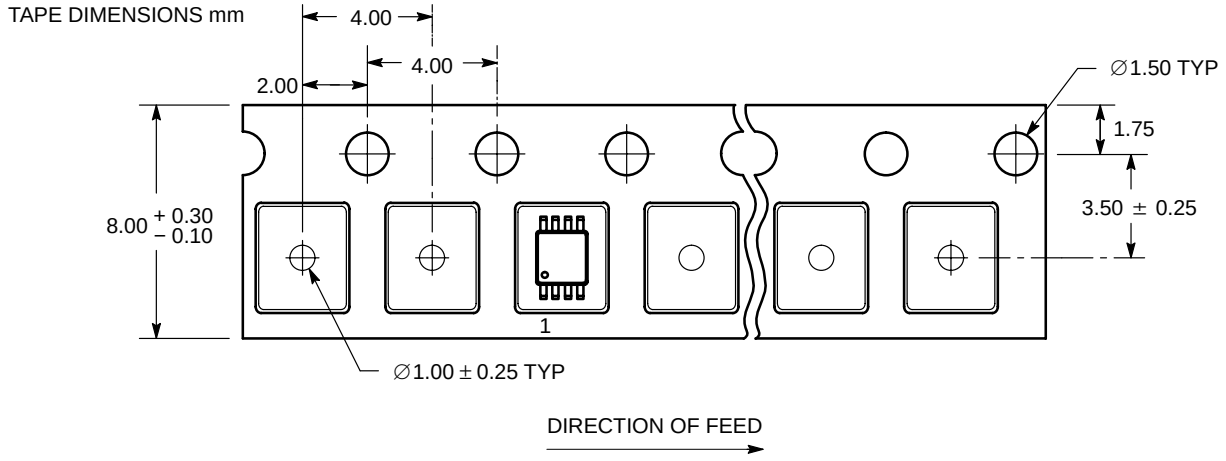


Figure 19. US8 Reel Configuration/Orientation

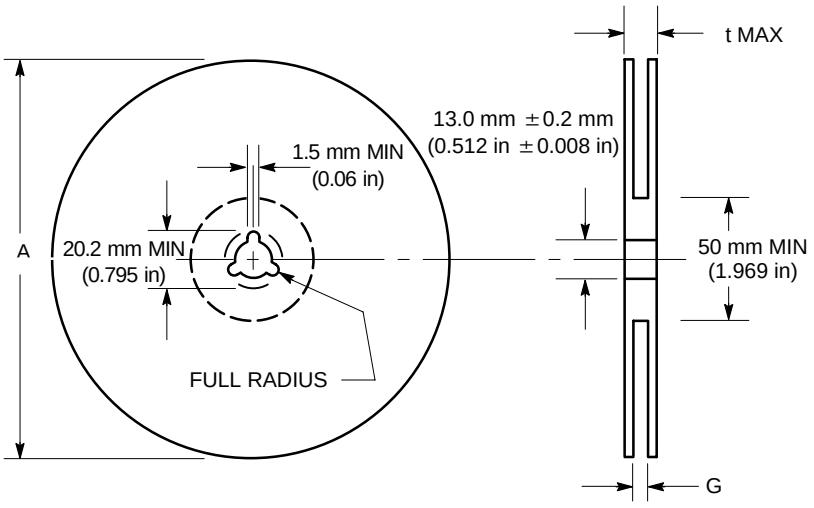


Figure 20. Reel Dimensions

REEL DIMENSIONS

Tape Size	T and R Suffix	A Max	G	t Max
8 mm	US	178 mm (7 in)	8.4 mm, + 1.5 mm, −0.0 (0.33 in + 0.059 in, −0.00)	14.4 mm (0.56 in)

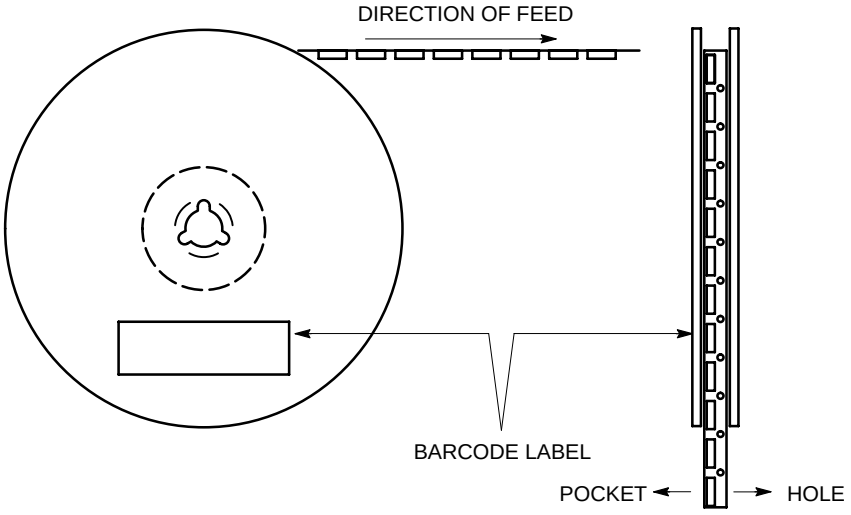
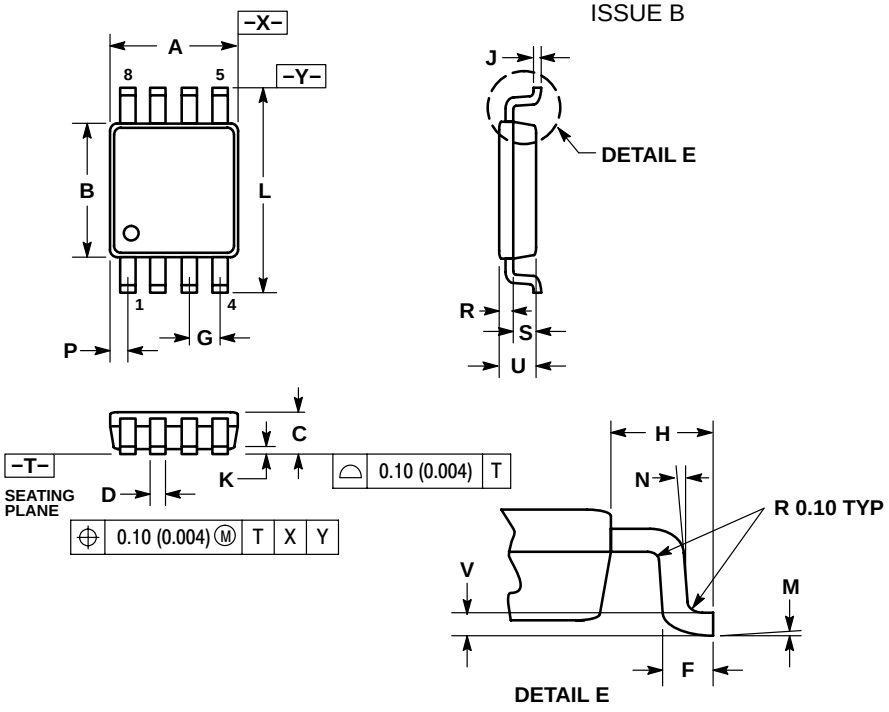


Figure 21. Reel Winding Direction

PACKAGE DIMENSIONS

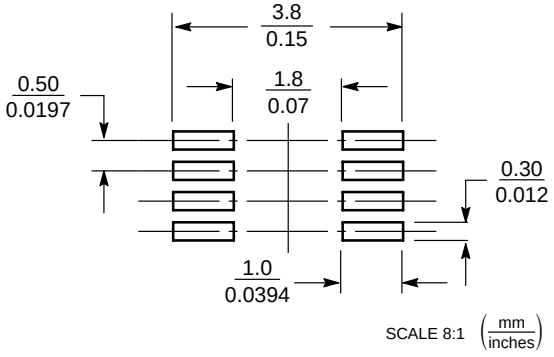
US8
US SUFFIX
CASE 493−02
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION “A” DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.140 MM (0.0055”) PER SIDE.
4. DIMENSION “B” DOES NOT INCLUDE INTER−LEAD FLASH OR PROTRUSION. INTER−LEAD FLASH AND PROTRUSION SHALL NOT E3XCEED 0.140 (0.0055”) PER SIDE.
5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076−0.0203 MM. (300−800 ”).
6. ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002 “).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.90	2.10	0.075	0.083
B	2.20	2.40	0.087	0.094
C	0.60	0.90	0.024	0.035
D	0.17	0.25	0.007	0.010
F	0.20	0.35	0.008	0.014
G	0.50 BSC		0.020 BSC	
H	0.40 REF		0.016 REF	
J	0.10	0.18	0.004	0.007
K	0.00	0.10	0.000	0.004
L	3.00	3.20	0.118	0.126
M	0 °	6 °	0 °	6 °
N	5 °	10 °	5 °	10 °
P	0.23	0.34	0.010	0.013
R	0.23	0.33	0.009	0.013
S	0.37	0.47	0.015	0.019
U	0.60	0.80	0.024	0.031
V	0.12 BSC		0.005 BSC	

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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Order Literature: http://www.onsemi.com/litorder

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